Freescale Semiconductor
Technical Data

Document Number: MRF6S23140H
Rev. 1, 5/2006

√RoHS

RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

MRF6S23140HR3
MRF6S23140HSR3

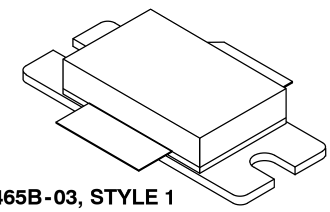
Designed for CDMA base station applications with frequencies from 2300 to 2400 MHz. Suitable for WiMAX, WiBro and multicarrier amplifier applications. To be used in Class AB and Class C WLL applications.

- Typical 2-Carrier W-CDMA Performance: V_{DD} = 28 Volts, I_{DQ} = 1300 mA, P_{out} = 28 Watts Avg., Full Frequency Band, Channel Bandwidth = 3.84 MHz, PAR = 8.5 dB @ 0.01% Probability on CCDF.
  - Power Gain — 15.2 dB
  - Drain Efficiency — 25%
  - IM3 @ 10 MHz Offset — -37 dBc in 3.84 MHz Channel Bandwidth
  - ACPR @ 5 MHz Offset — -40 dBc in 3.84 MHz Channel Bandwidth
- Capable of Handling 10:1 VSWR, @ 32 Vdc, 2390 MHz, 140 Watts CW Output Power

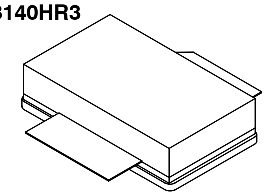
Features

- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32 V_{DD} Operation
- Integrated ESD Protection
- Lower Thermal Resistance Package
- Designed for Lower Memory Effects and Wide Instantaneous Bandwidth Applications
- Low Gold Plating Thickness on Leads, 40μ″ Nominal.
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

2300-2400 MHz, 28 W AVG., 28 V
2 x W-CDMA
LATERAL N-CHANNEL
RF POWER MOSFETs



CASE 465B-03, STYLE 1
NI-880
MRF6S23140HR3



CASE 465C-02, STYLE 1
NI-880S
MRF6S23140HSR3

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +68	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +12	Vdc
Storage Temperature Range	T_{stg}	- 65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature	T_J	200	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (1,2)	Unit
Thermal Resistance, Junction to Case Case Temperature 82°C, 140 W CW Case Temperature 75°C, 28 W CW	$R_{\theta JC}$	 0.29 0.33	°C/W

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	2 (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

1. MTTF calculator available at http://www.freescale.com/rf. Select Tools/Software/Application Software/Calculators to access the MTTF calculators by product.
2. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers.* Go to http://www.freescale.com/rf. Select Documentation/Application Notes - AN1955.

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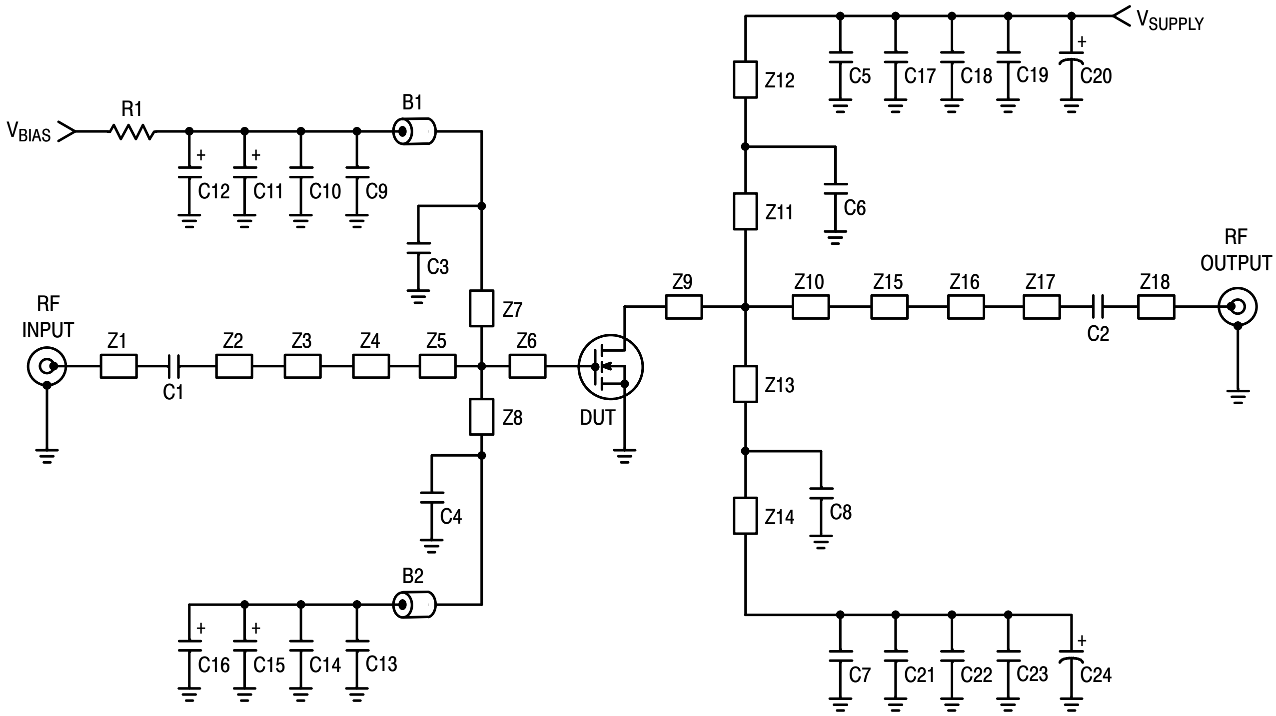
Table 4. Electrical Characteristics (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Zero Gate Voltage Drain Leakage Current (V_{DS} = 68 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current (V_{DS} = 28 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current (V_{GS} = 5 Vdc, V_{DS} = 0 Vdc)	I_{GSS}	—	—	500	nAdc
On Characteristics					
Gate Threshold Voltage (V_{DS} = 10 Vdc, I_D = 300 μAdc)	$V_{GS(th)}$	1	2	3	Vdc
Gate Quiescent Voltage (V_{DS} = 28 Vdc, I_D = 1300 mAdc)	$V_{GS(Q)}$	2	2.8	4	Vdc
Drain-Source On-Voltage (V_{GS} = 10 Vdc, I_D = 3 Adc)	$V_{DS(on)}$	0.1	0.21	0.3	Vdc
Dynamic Characteristics (1)					
Reverse Transfer Capacitance (V_{DS} = 28 Vdc ± 30 mV(rms)ac @ 1 MHz, V_{GS} = 0 Vdc)	C_{rss}	—	2	—	pF
Functional Tests (In Freescale Test Fixture, 50 ohm system) V_{DD} = 28 Vdc, I_{DQ} = 1300 mA, P_{out} = 28 W Avg., f1 = 2300 MHz, f2 = 2310 MHz and f1 = 2390 MHz, f2 = 2400 MHz, 2-Carrier W-CDMA, 3.84 MHz Channel Bandwidth Carriers. ACPR measured in 3.84 MHz Channel Bandwidth @ ±5 MHz Offset. IM3 measured in 3.84 MHz Bandwidth @ ±10 MHz Offset. PAR = 8.5 dB @ 0.01% Probability on CCDF.					
Power Gain	G_{ps}	13	15.2	17	dB
Drain Efficiency	η_D	23	25	—	%
Intermodulation Distortion	IM3	—	-37	-35	dBc
Adjacent Channel Power Ratio	ACPR	—	-40	-38	dBc
Input Return Loss	IRL	—	-15	—	dB

1. Part internally matched both on input and output.

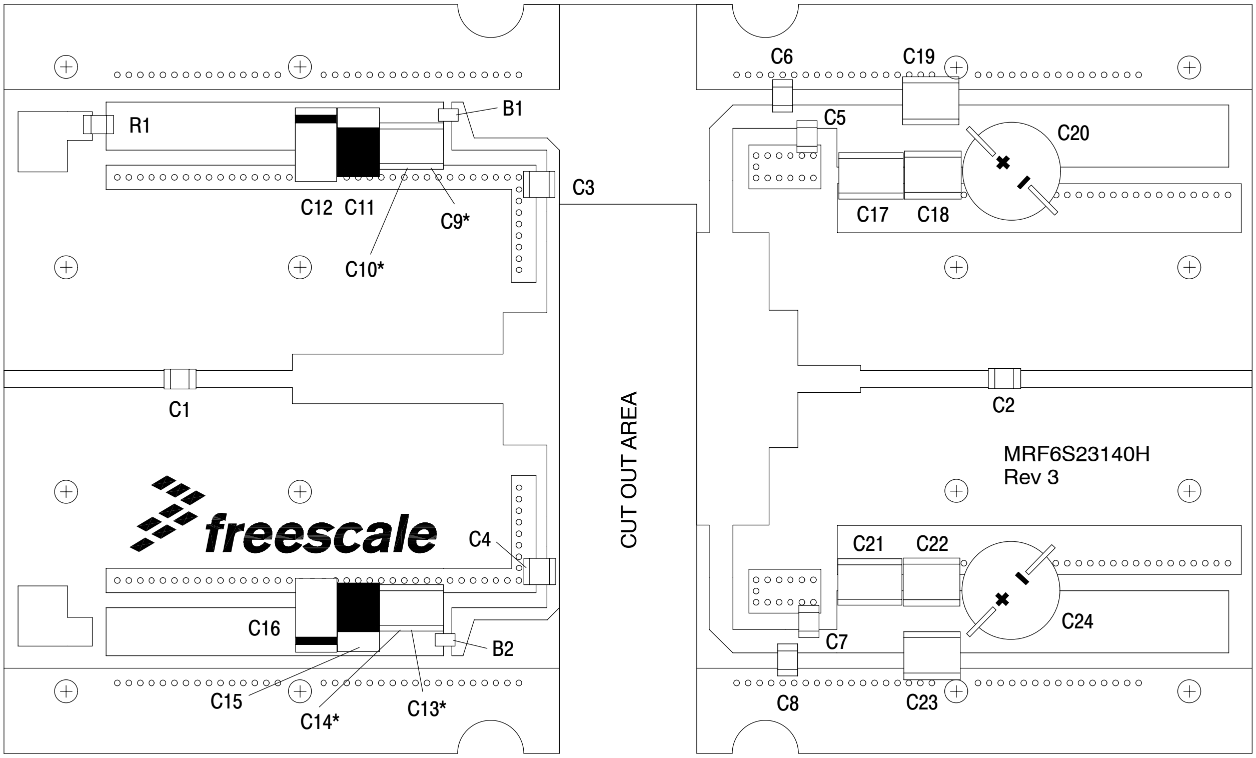


Z1	0.678″ x 0.068″ Microstrip	Z10	0.193″ x 1.170″ Microstrip
Z2	0.420″ x 0.068″ Microstrip	Z11, Z13	0.712″ x 0.095″ Microstrip
Z3	0.845″ x 0.200″ Microstrip	Z12, Z14	0.098″ x 0.095″ Microstrip
Z4	0.175″ x 0.530″ Microstrip	Z15	0.115″ x 0.550″ Microstrip
Z5, Z6	0.025″ x 0.530″ Microstrip	Z16	0.250″ x 0.110″ Microstrip
Z7	0.514″ x 0.050″ Microstrip	Z17	0.539″ x 0.068″ Microstrip
Z8	0.507″ x 0.050″ Microstrip	Z18	0.956″ x 0.068″ Microstrip
Z9	0.097″ x 1.170″ Microstrip	PCB	Taconic RF-35, 0.030″, ε_r = 3.5

Figure 1. MRF6S23140HR3(SR3) Test Circuit Schematic

Table 5. MRF6S23140HR3(SR3) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1, B2	Ferrite Beads, Short	2743019447	Fair-Rite
C1, C2, C3, C4, C5, C6, C7, C8	5.6 pF 100B Chip Capacitors	100B5R6CP500X	ATC
C9, C13	0.01 μF, 100 V Chip Capacitors	C1825C103J1RAC	Kemet
C10, C14, C17, C21	2.2 μF, 50 V Chip Capacitors	C1825C225J5RAC	Kemet
C11, C15	22 μF, 25 V Tantalum Chip Capacitors	ECS-T1ED226R	Panasonic TE series
C12, C16	47 μF, 16 V Tantalum Chip Capacitors	T491D476K016AS	Kemet
C18, C19, C22, C23	10 μF, 50 V Chip Capacitors (2220)	GRM55DR61H106KA88B	Murata
C20, C24	330 μF, 63 V Electrolytic Capacitors	NACZF331M63V	Nippon
R1	10 Ω, 1/8 W Chip Resistor (1206)		



* Stacked

Figure 2. MRF6S23140HR3(SR3) Test Circuit Component Layout

TYPICAL CHARACTERISTICS

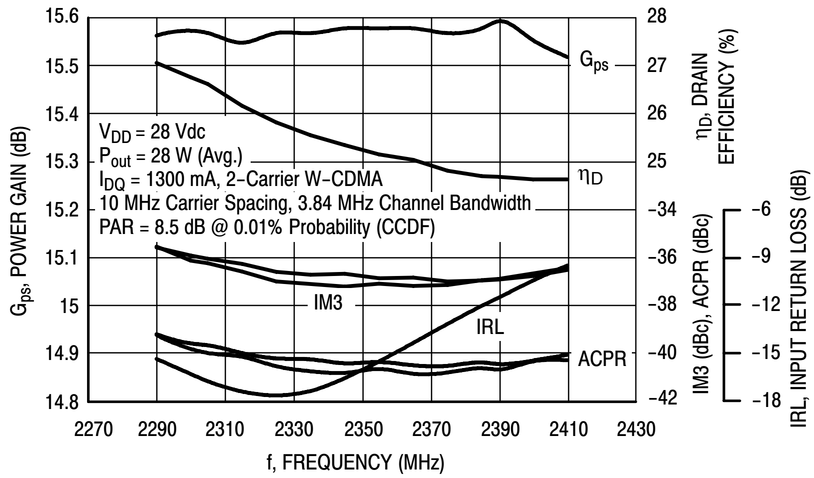


Figure 3. 2-Carrier W-CDMA Broadband Performance @ P_{out} = 28 Watts Avg.

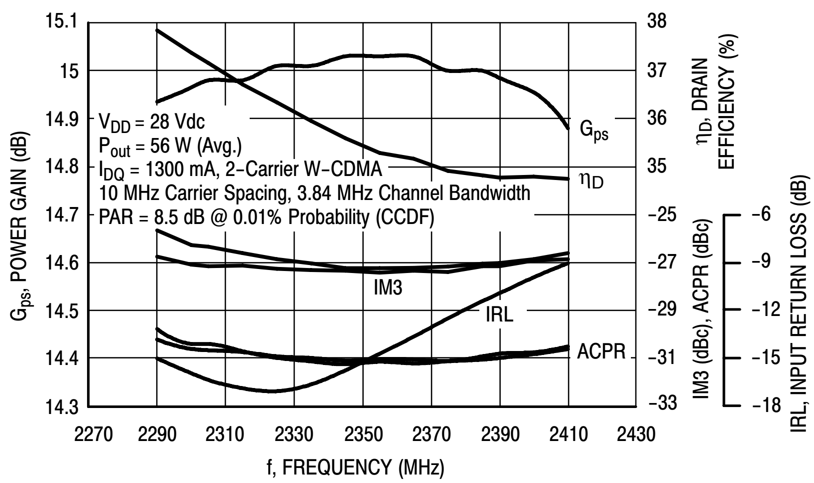


Figure 4. 2-Carrier W-CDMA Broadband Performance @ P_{out} = 56 Watts Avg.

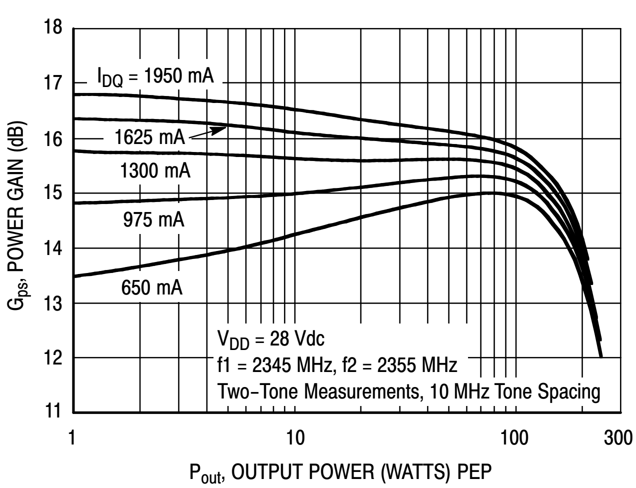


Figure 5. Two-Tone Power Gain versus Output Power

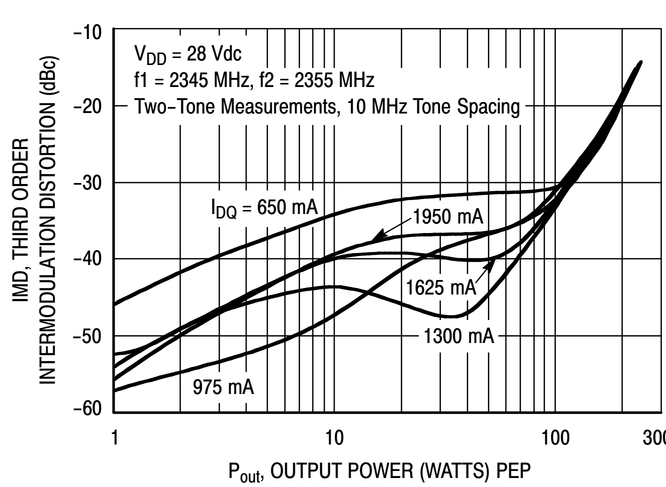


Figure 6. Third Order Intermodulation Distortion versus Output Power

TYPICAL CHARACTERISTICS

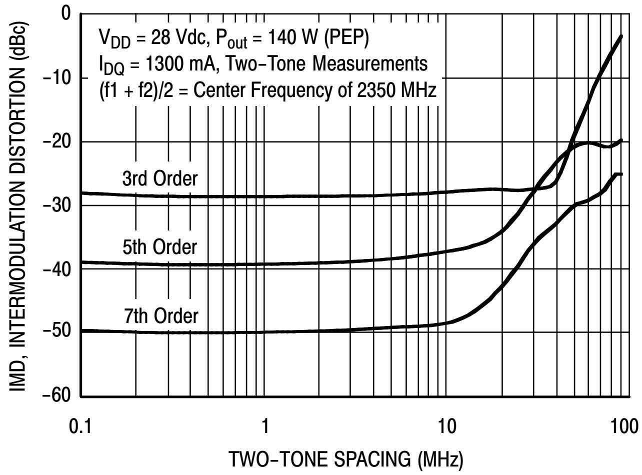


Figure 7. Intermodulation Distortion Products versus Tone Spacing

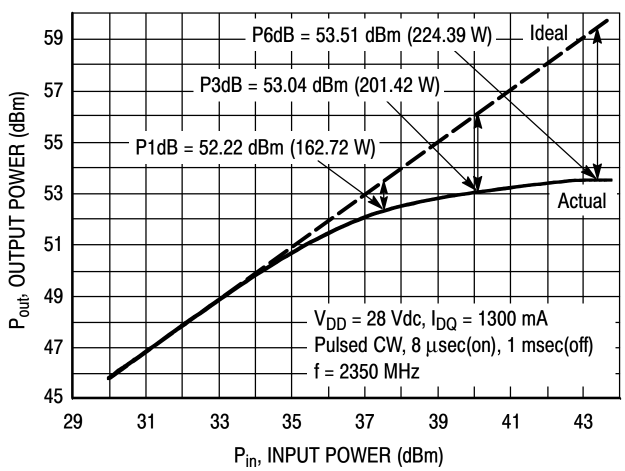


Figure 8. Pulse CW Output Power versus Input Power

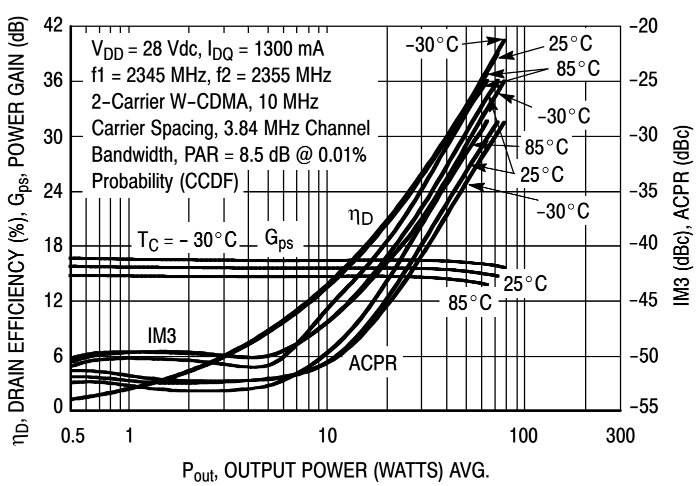


Figure 9. 2-Carrier W-CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power

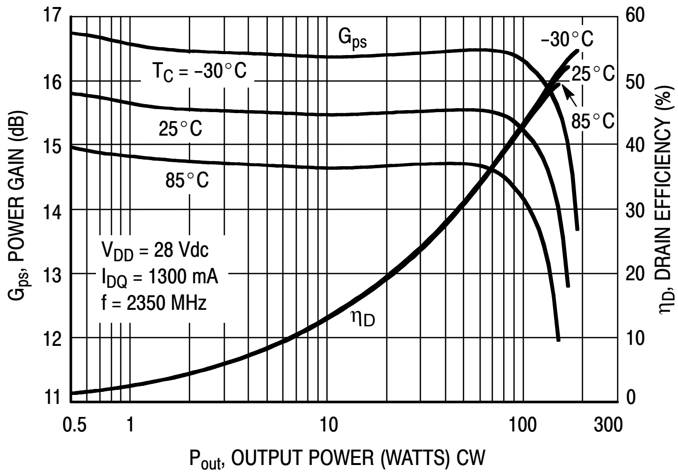


Figure 10. Power Gain and Drain Efficiency versus Output Power

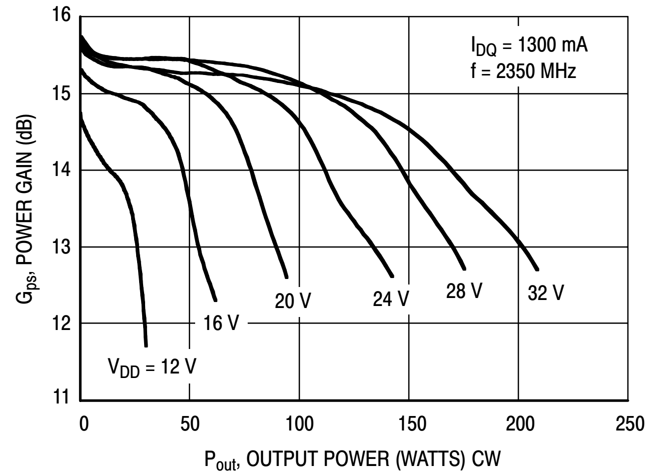
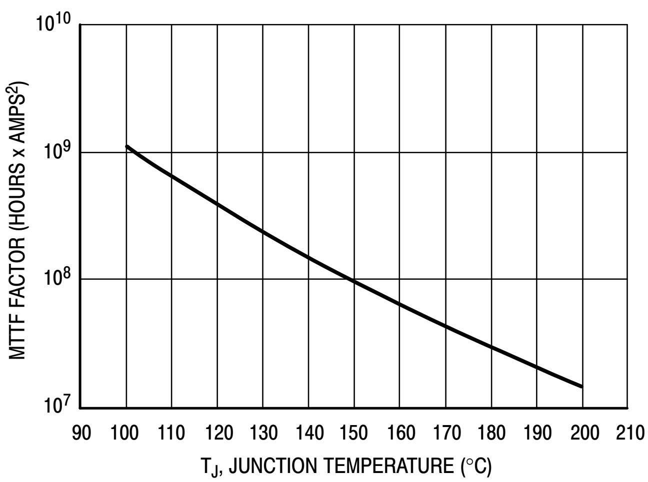


Figure 11. Power Gain versus Output Power



This above graph displays calculated MTTF in hours x ampere^2 drain current. Life tests at elevated temperatures have correlated to better than ±10% of the theoretical prediction for metal failure. Divide MTTF factor by I_D^2 for MTTF in a particular application.

Figure 12. MTTF Factor versus Junction Temperature

W-CDMA TEST SIGNAL

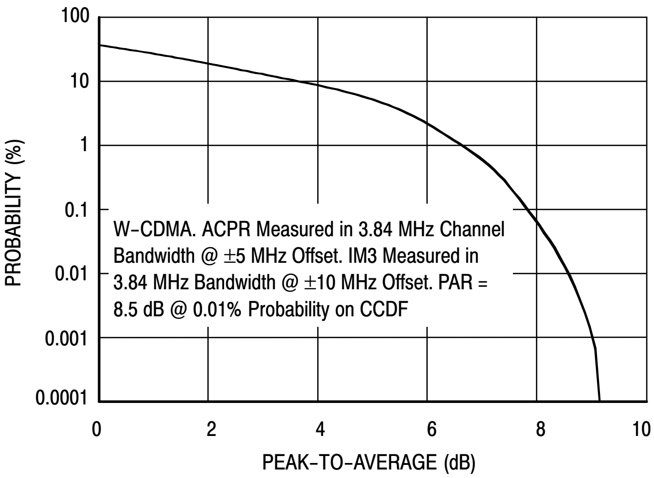


Figure 13. CCDF W-CDMA 3GPP, Test Model 1, 64 DPCH, 67% Clipping, Single-Carrier Test Signal

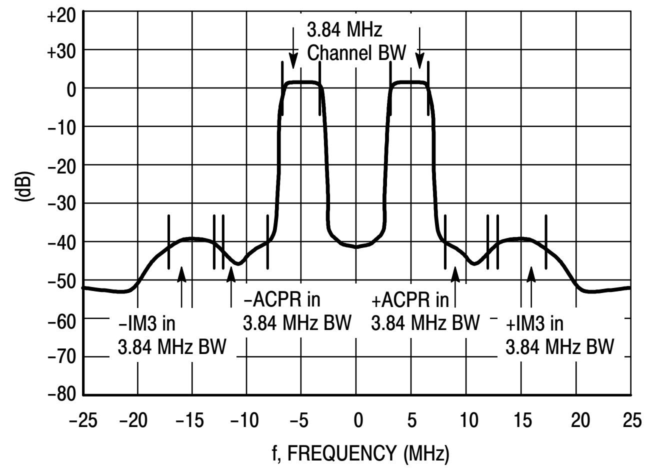
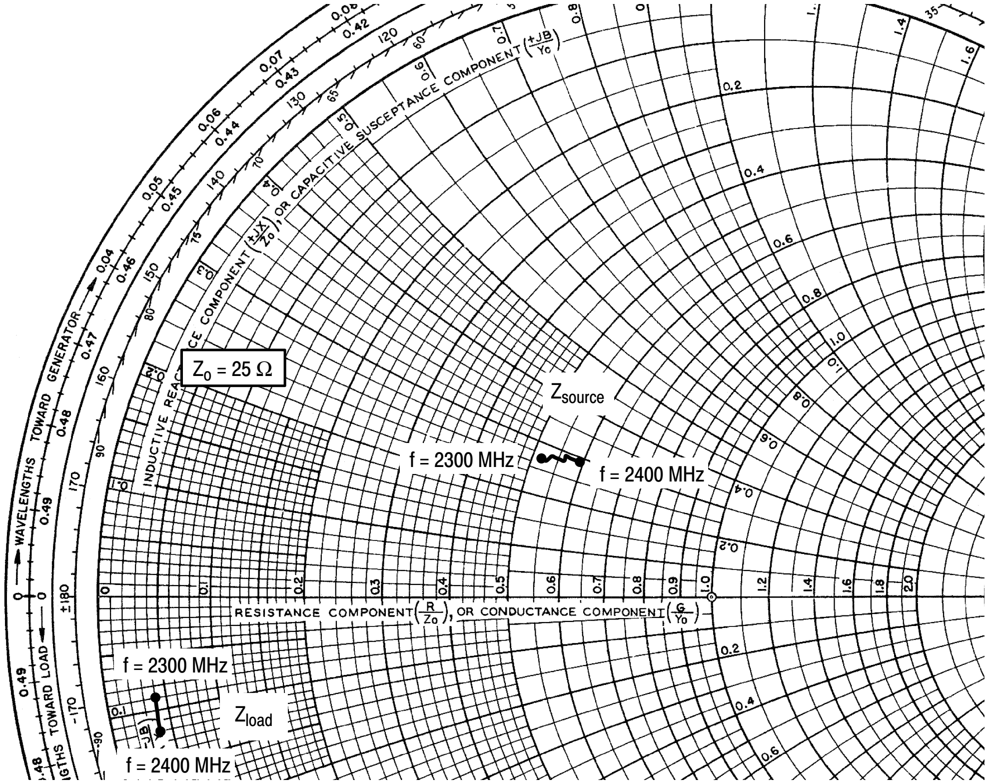


Figure 14. 2-Carrier W-CDMA Spectrum



V_{DD} = 28 Vdc, I_{DQ} = 1300 mA, P_{out} = 28 W Avg.

f MHz	Z_{source} Ω	Z_{load} Ω
2300	12.92 + j6.65	1.05 - j2.88
2310	13.06 + j6.73	1.04 - j2.82
2320	13.21 + j6.80	1.03 - j2.76
2330	13.37 + j6.87	1.01 - j2.70
2340	13.53 + j6.94	1.00 - j2.64
2350	13.70 + j7.01	0.99 - j2.58
2360	13.88 + j7.08	0.97 - j2.52
2370	14.06 + j7.14	0.96 - j2.46
2380	14.25 + j7.21	0.95 - j2.40
2390	14.45 + j7.27	0.94 - j2.34
2400	14.66 + j7.33	0.93 - j2.28

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

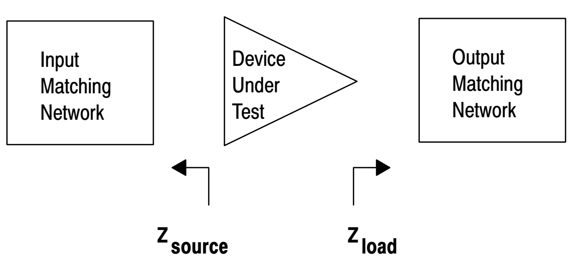
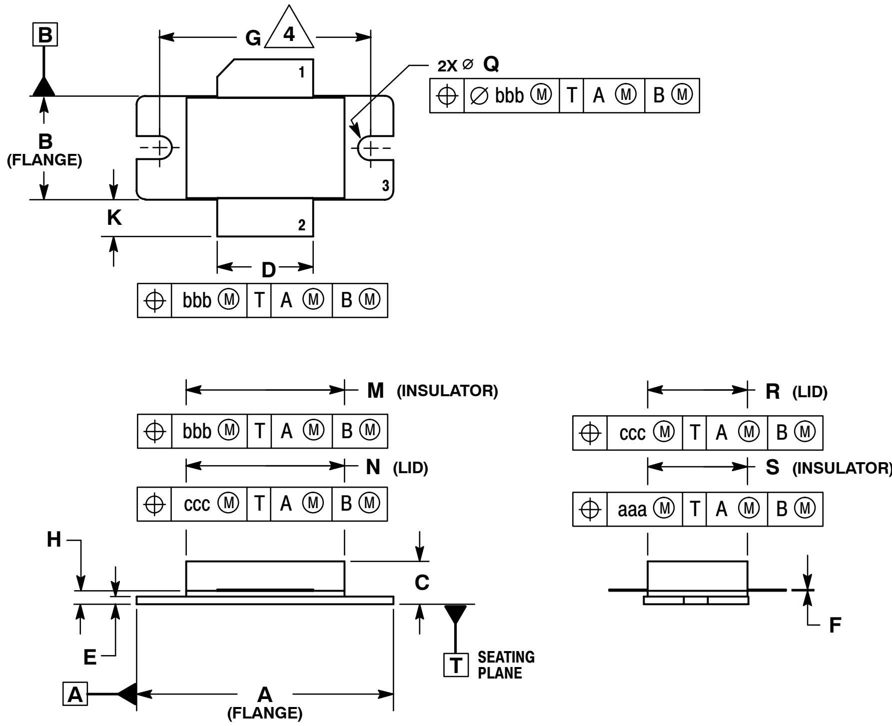


Figure 15. Series Equivalent Source and Load Impedance

NOTES

PACKAGE DIMENSIONS

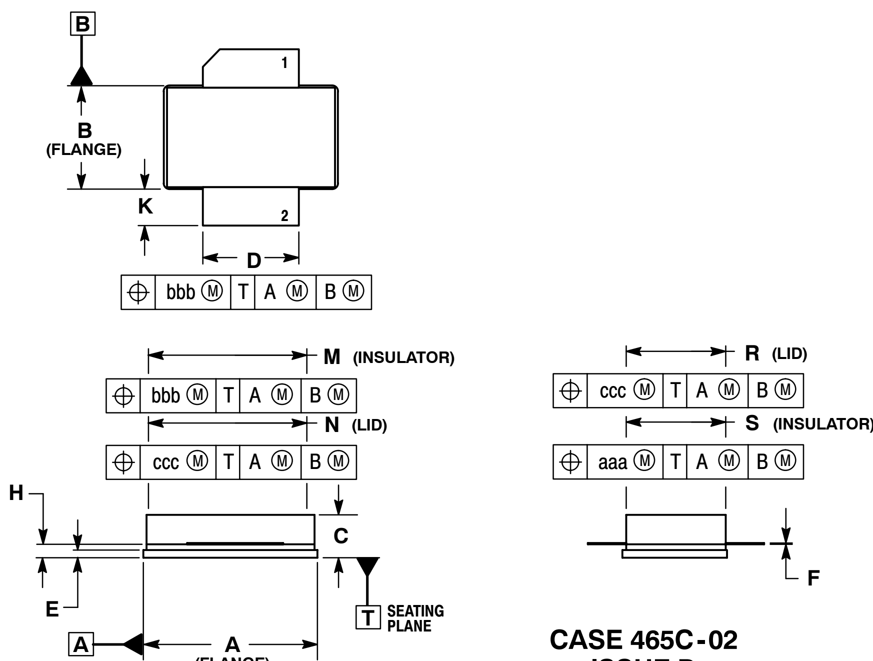


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M−1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.
4. RECOMMENDED BOLT CENTER DIMENSION OF 1.16 (29.57) BASED ON M3 SCREW.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.535	0.545	13.6	13.8
C	0.147	0.200	3.73	5.08
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.175	0.205	4.44	5.21
M	0.872	0.888	22.15	22.55
N	0.871	0.889	19.30	22.60
Q	Ø.118	Ø.138	Ø3.00	Ø3.51
R	0.515	0.525	13.10	13.30
S	0.515	0.525	13.10	13.30
aaa	0.007 REF		0.178 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

CASE 465B-03
ISSUE E
NI-880
MRF6S23140HR3



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	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.905	0.915	22.99	23.24
B	0.535	0.545	13.60	13.80
C	0.147	0.200	3.73	5.08
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.872	0.888	22.15	22.55
N	0.871	0.889	19.30	22.60
R	0.515	0.525	13.10	13.30
S	0.515	0.525	13.10	13.30
aaa	0.007 REF		0.178 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

CASE 465C-02
ISSUE D
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